

a spacer layer on at least part of the surface of said barrier layer between said gate and said drain electrode and between said gate and said source electrode;

a field plate on said spacer layer and extending on said spacer over said barrier layer and toward said drain electrode, and extending on said spacer layer over said barrier layer and toward said source electrode; and

at least one conductive path electrically connecting said field plate to said source electrode or said gate.

**24.** A metal semiconductor field effect transistor (MES-FET), comprising:

a buffer layer on a substrate;

a channel layer on said buffer layer with said buffer layer sandwiched between said channel layer and substrate;

a source electrode in electrical contact with said channel layer;

a drain electrode also in electrical contact with said channel layer;

a gate in electrical contact with said channel layer between said source and drain electrodes;

a spacer layer on at least part of the surface of said channel layer between said gate and said drain electrode and between said gate and said source electrode;

a field plate on said spacer layer and extending on said spacer over said channel layer and toward said drain electrode, and extending on said spacer layer over said channel layer and toward said source electrode; and

at least one conductive path electrically connecting said field plate to said source electrode or said gate.

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